HIGH-SPEED, FULLY DIFFERENTIAL, CONTINUOUSLY VARIABLE GAIN AMPLIFIER

Check for Samples: THS7530

FEATURES

- **Low Noise: V_n = 1.1 nV/$\sqrt{\text{Hz}}$, Noise Figure = 9 dB**
- **Low Distortion:**
  - **- HD_2 = -65 dBc, HD_3 = -61 dBc at 32 MHz**
  - **- IMD_3 = -62 dBc, OIP_3 = 21 dBm at 70 MHz**
- **300 MHz Bandwidth**
- **Continuously Variable Gain Range: 11.6 dB to 46.5 dB**
- **Gain Slope: 38.8 dB/V**
- **Fully Differential Input and Output**
- **Output Common-Mode Voltage Control**
- **Output Voltage Limiting**

APPLICATIONS

- **Time Gain Amplifiers in Ultra Sound, Sonar, and Radar**
- **Automatic Gain Control in Communication and Video**
- **System Gain Calibration in Communications**
- **Variable Gain in Instrumentation**
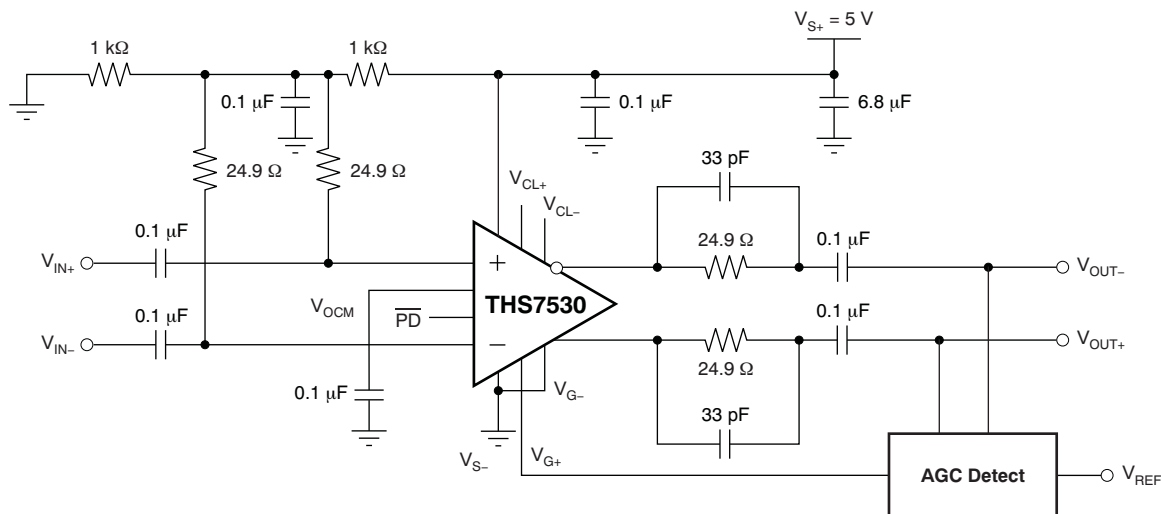
DESCRIPTION

The THS7530 is fabricated using Texas Instruments' state-of-the-art BiCom III SiGe complementary bipolar process. The THS7530 is a dc-coupled, wide bandwidth amplifier with voltage-controlled gain. The amplifier has high-impedance differential inputs and low-impedance differential outputs with high bandwidth gain control, output common-mode control, and output voltage clamping.

Signal channel performance is exceptional with 300-MHz bandwidth, and third harmonic distortion of –61 dBc at 32 MHz with 1-V_{PP} output into 400 Ω.

Gain control is linear in dB with 0 V to 0.9 V varying the gain from 11.6 dB to 46.5 dB with 38.8-dB/V gain slope.

Output voltage limiting is provided to limit the output voltage swing, and prevent saturating following stages.

The device is characterized for operation over the industrial temperature range, –40°C to +85°C.

This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

PACKAGING/ORDERING INFORMATION[1]

PART NUMBER	PACKAGE TYPE	PACKAGE MARKING	TRANSPORT MEDIA, QUANTITY
THS7530PWP	TSSOP-14-PP	THS7530	Rails, 90
THS7530PWPR			Tape and Reel, 2000

(1)   For the most current package and ordering information, see the Package Option Addendum at the end of this document or see the TI web site at www.ti.com.

ABSOLUTE MAXIMUM RATINGS[1]

Over operating free-air temperature range, unless otherwise noted.

		THS7530
$V_{S+} - V_{S-}$	Supply voltage	5.5 V
V_I	Input voltage	$\pm V_S$
I_O	Output current	65 mA
V_{ID}	Differential input voltage	± 4 V
	Continuous power dissipation	See Dissipation Rating Table
T_J	Maximum junction temperature	+150°C
	Maximum junction temperature for long term stability[2]	+125°C
T_{stg}	Storage temperature range	−65°C to +150°C
ESD	HBM	3000 V
	CDM	1500 V
	MM	200 V

(1)   The absolute maximum ratings under any condition is limited by the constraints of the silicon process. Stresses above these ratings may cause permanent damage. Exposure to absolute maximum conditions for extended periods may degrade device reliability. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those specified is not implied.
(2)   The maximum junction temperature for continuous operation is limited by package constraints. Operation above this temperature may result in reduced reliability and/or lifetime of the device.

PACKAGE THERMAL DATA

PACKAGE	PCB	θ_{JA} (°C/W)	θ_{JC} (°C/W)[1]	$T_A = 25$°C POWER RATING[2]
PWP (14-pin)[3]	See *Layout Considerations* in the Application section of this data sheet.	37.5	2.07	3 W

(1)   This data was taken using the JEDEC High-K test printed circuit board (PCB).
(2)   This data was taken using 2 oz. trace and copper pad that is soldered directly to a 3 in x 3 in PCB.
(3)   The THS7530 incorporates a PowerPAD™ on the underside of the chip. This acts as a heatsink and must be connected to a thermally dissipative plane for proper power dissipation. Failure to do so may result in exceeding the maximum junction temperature which could permanently damage the device. See TI technical briefs SLMA002 and SLMA004 for more information about using the PowerPAD thermally enhanced package.

RECOMMENDED OPERATING CONDITIONS

		TEST CONDITIONS	MIN	TYP	MAX	UNIT
$[V_{S-}$ to $V_{S+}]$	Supply voltage		4.5	5	5.5	V
T_A	Operating free-air temperature		−40		+85	°C
	Input common mode voltage	$[V_{S-}$ to $V_{S+}] = 5$ V		2.5		V
	Output common mode voltage	$[V_{S-}$ to $V_{S+}] = 5$ V		2.5		V

SPECIFICATIONS: MAIN AMPLIFIER

V_{S+} = 5 V, V_{S-} = 0 V, V_{OCM} = 2.5 V, V_{ICM} = 2.5 V, V_{G-} = 0 V, V_{G+} = 1 V (maximum gain), T_A = 25°C, ac performance measured using the ac test circuit shown in Figure 1 (unless otherwise noted). DC performance is measured using the dc test circuit shown in Figure 2 (unless otherwise noted)

PARAMETER	TEST CONDITIONS	TYP	OVER TEMPERATURE			
		+25°C	+25°C	-40°C to +85°C	UNITS	MIN/MAX
AC PERFORMANCE (See Figure 1)						
Small-signal bandwidth	All gains, P_{IN} = −45 dBm	300			MHz	Typ
Slew rate[1]	1-V_{PP} Step, 25% to 75%, minimum gain	1250			V/µs	Typ
Settling time to 1% [1]	1-V_{PP} Step, minimum gain	11			ns	Typ
Harmonic distortion	$V_{O(PP)}$ = 1 V, $R_{L(diff)}$= 400 Ω					
2nd Harmonic	f = 32 MHz	−65			dBc	Typ
3rd Harmonic	f = 32 MHz	−61			dBc	Typ
Third-order intermodulation distortion	P_O = −10 dBm each tone, f_C= 70 MHz, 200-kHz tone spacing	−62			dBc	Typ
Third-order output intercept point	f_C= 70 MHz, 200-kHz tone spacing	21			dBm	Typ
Noise figure (with input termination)	Source impedance: 50 Ω	9			dB	Typ
Total input voltage noise	f > 100 kHz	1.1			nV/√Hz	Typ
DC PERFORMANCE—INPUTS (See Figure 2)						
Input bias current		20	39	40	µA	Max
Input bias current offset		<150			pA	Typ
Minimum input voltage	Minimum gain	1.5	1.6	1.7	V	Max
Maximum input voltage	Minimum gain	3.5	3.35	3.2	V	Min
Common-mode rejection ratio		114	56	44	dB	Min
Differential input impedance		8.5 || 3.0			kΩ || pF	Typ
DC PERFORMANCE—OUTPUTS (See Figure 2)						
Output offset voltage	All gains	±100	±340	±480	mV	Max
Maximum output voltage high		3.5	3.275	3.25	V	Min
Minimum output voltage low		1.5	1.7	1.8	V	Max
Output current		±37	±16	±16	mA	Min
Output impedance		15			Ω	Typ
OUTPUT COMMON-MODE VOLTAGE CONTROL (See Figure 2)						
Small-signal bandwidth		32			MHz	Typ
Gain		1.00			V/V	Typ
Common-mode offset voltage		4.5	12	13.8	mV	Max
Minimum input voltage		1.75			V	Typ
Maximum input voltage		3.25			V	Typ
Input impedance		25 || 1			kΩ || pF	Typ
Default voltage, with no connect		2.5			V	Typ
Input bias current		<1			µA	Typ

(1) Slew rate and settling time measured at amplifier output.

SPECIFICATIONS: MAIN AMPLIFIER (continued)

V_{S+} = 5 V, V_{S-} = 0 V, V_{OCM} = 2.5 V, V_{ICM} = 2.5 V, V_{G-} = 0 V, V_{G+} = 1 V (maximum gain), T_A = 25°C, ac performance measured using the ac test circuit shown in Figure 1 (unless otherwise noted). DC performance is measured using the dc test circuit shown in Figure 2 (unless otherwise noted)

PARAMETER		TEST CONDITIONS	TYP +25°C	OVER TEMPERATURE +25°C	OVER TEMPERATURE -40°C to +85°C	UNITS	MIN/ MAX
GAIN CONTROL (See Figure 2)							
Gain control differential voltage range		V_{G+}	0 to 1			V	Typ
Minus gain control voltage		$V_{G-} - V_{S-}$	−0.6 to 0.8			V	Typ
Minimum gain		V_{G+} = 0 V	11.6			dB	Typ
Maximum gain		V_{G+} = 0.9 V	46.5			dB	Typ
Gain slope		V_{G+} = 0 V to 0.9 V	38.8			dB/V	Typ
Gain slope variation		V_{G+} = 0 V to 0.9 V	±1.5			dB/V	Typ
Gain error		V_{G+} = 0 V to 0.15 V	±4			dB	Typ
		V_{G+} = 0.15 V to 0.9 V	±2.25			dB	Typ
Gain control input bias current			<1			µA	Typ
Gain control input resistance			40			kΩ	Typ
Gain control bandwidth		Small signal −3 dB	15			MHz	Typ
VOLTAGE CLAMPING (See Figure 2)							
Output voltages ($V_{OUT±}$) relative to clamp voltages ($V_{CL±}$)		In voltage limiting mode	±25	±38	±60	mV	Max
$V_{CL±}$	Input resistance		3.3			kΩ	Typ
	Voltage limits		V_{S-} to V_{S+}			V	Typ
POWER SUPPLY (See Figure 2)							
Specified operating voltage			5	5.5	5.5	V	Max
Maximum quiescent current			40	48	49	mA	Max
Power supply rejection (±PSRR)			77	70	45	dB	Min
POWERDOWN (See Figure 2)							
Enable voltage threshold		TTL low = shut down	1.4		1.0	V	Min
Disable voltage threshold		TTL high = normal operation	1.4		1.65	V	Max
Power-down quiescent current			0.35	0.4	0.45	mA	Max
Input current high			9	16	19	µA	Max
Input current low			109	116	119	µA	Max
Input impedance			50 ‖ 1			kΩ ‖ pF	Typ
Turn-on time delay		Measured to 50% quiescent current	820			ns	Typ
Turn-off time delay			500			ns	Typ
Forward isolation in power down			80			dB	Typ
Input resistance in power down			> 1			MΩ	Typ
Output resistance in power down			16			kΩ	Typ

Product Folder Link(s): *THS7530*
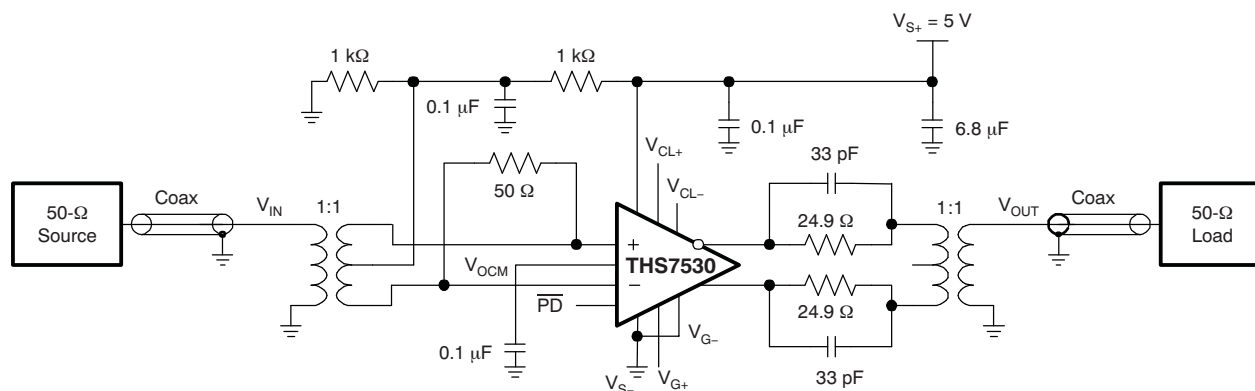
Figure 1. AC Test Circuit
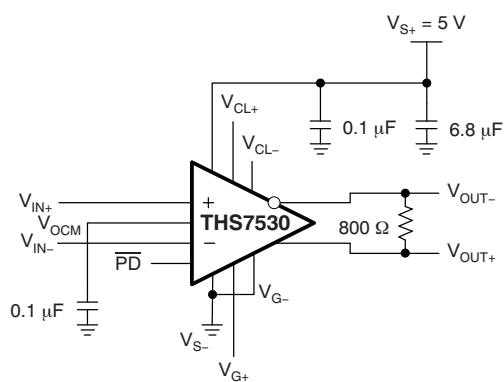
Figure 2. DC Test Circuit

PIN ASSIGNMENTS

TSSOP PACKAGE
PWP-14
(TOP VIEW)

```
        ┌───○────┐
   NC │ 1      14 │ V_CL+
   NC │ 2      13 │ V_CL−
 V_IN+ │ 3      12 │ V_OCM
 V_IN− │ 4      11 │ V_OUT−
  V_G+ │ 5      10 │ V_OUT+
  V_G− │ 6       9 │ V_S+
    PD │ 7       8 │ V_S−
        └─────────┘
```
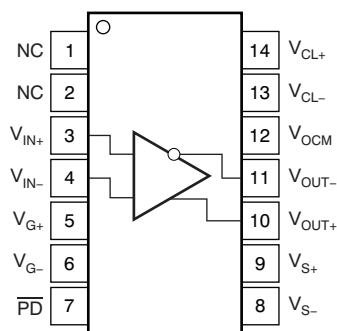
Table 1. Terminal Functions

TERMINAL		DESCRIPTION
NO.	NAME	
1	NC	No internal connection
2	NC	No internal connection
3	V_{IN+}	Noninverting amplifier input
4	V_{IN-}	Inverting amplifier input
5	V_{G+}	Gain setting positive input
6	V_{G-}	Gain setting negative input
7	$\overline{PD}$	Powerdown, $\overline{PD}$ = logic low puts part into low power mode; $\overline{PD}$ = logic high or open for normal operation
8	V_{S-}	Negative amplifier power-supply input
9	V_{S+}	Positive amplifier power-supply input
10	V_{OUT+}	Noninverted amplifier output
11	V_{OUT-}	Inverted amplifier output
12	V_{OCM}	Output common-mode voltage input
13	V_{CL-}	Output negative clamp voltage input
14	V_{CL+}	Output positive clamp voltage input

Product Folder Link(s): *THS7530*

THS7530

TYPICAL CHARACTERISTICS

Table of Graphs

Measured using the ac test circuit shown in Figure 1 (unless otherwise noted).

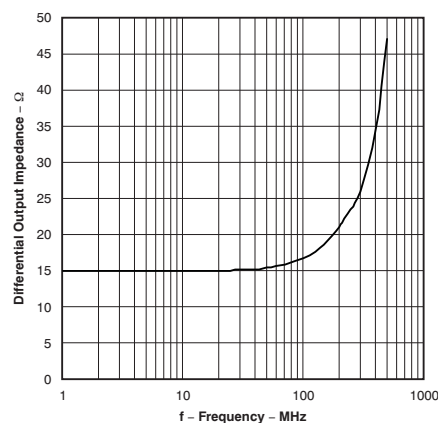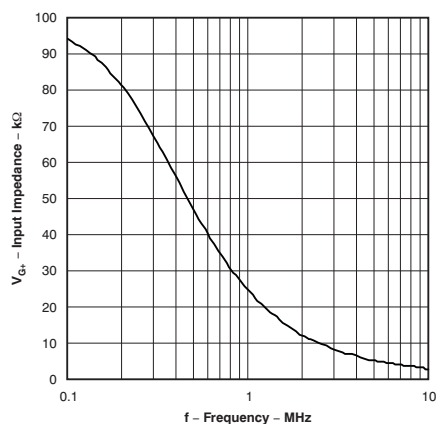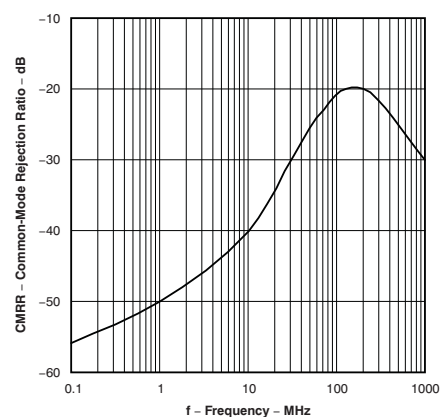|		Figure
Voltage Gain to Load	vs Frequency (Input at 45 dBm)	Figure 3
Gain and Gain Error	vs V_{G+}	Figure 4
Noise Figure	vs Frequency	Figure 5
Output Intercept Point	vs Frequency	Figure 6
1-dB Compression Point	vs Frequency	Figure 7
Total Input Voltage Noise	vs Frequency	Figure 8
Intermodulation Distortion	vs Frequency	Figure 9
Harmonic Distortion	vs Frequency	Figure 10
S-Parameters	vs Frequency	Figure 11
Differential Input Impedance of Main Amplifier	vs Frequency	Figure 12
Differential Output Impedance of Main Amplifier	vs Frequency	Figure 13
V_{G+} Input Impedance	vs Frequency	Figure 14
V_{OCM} Input Impedance	vs Frequency	Figure 15
Common-Mode Rejection Ratio	vs Frequency	Figure 16
Step Response: 2 V_{PP}	vs Time	Figure 17
Step Response: Rising Edge	vs Time	Figure 18
Step Response: Falling Edge	vs Time	Figure 19

TYPICAL CHARACTERISTICS

VOLTAGE GAIN TO LOAD
vs
FREQUENCY (P$_{IN}$ = −45 dBm)

Figure 3.

GAIN AND GAIN ERROR
vs
V$_{G+}$

Figure 4.

NOISE FIGURE
vs
FREQUENCY

Figure 5.

OUTPUT INTERCEPT POINT
vs
FREQUENCY

Figure 6.

1-dB COMPRESSION POINT
vs
FREQUENCY

Figure 7.

Product Folder Link(s): *THS7530*
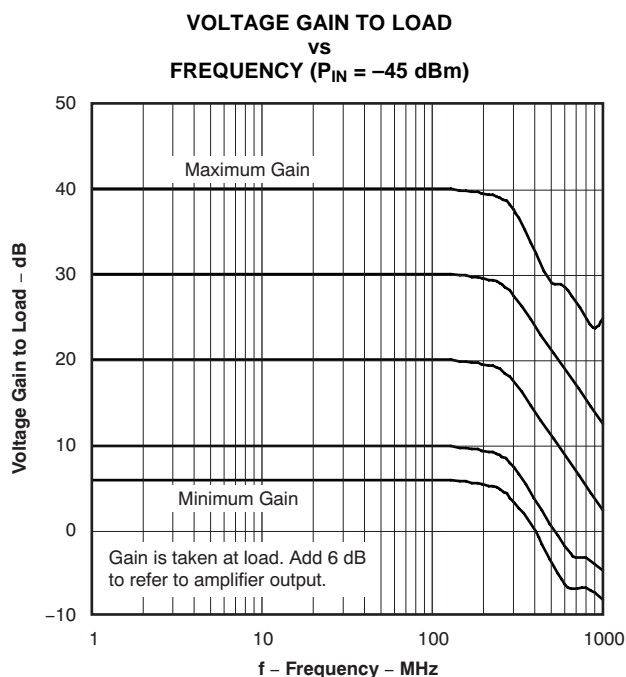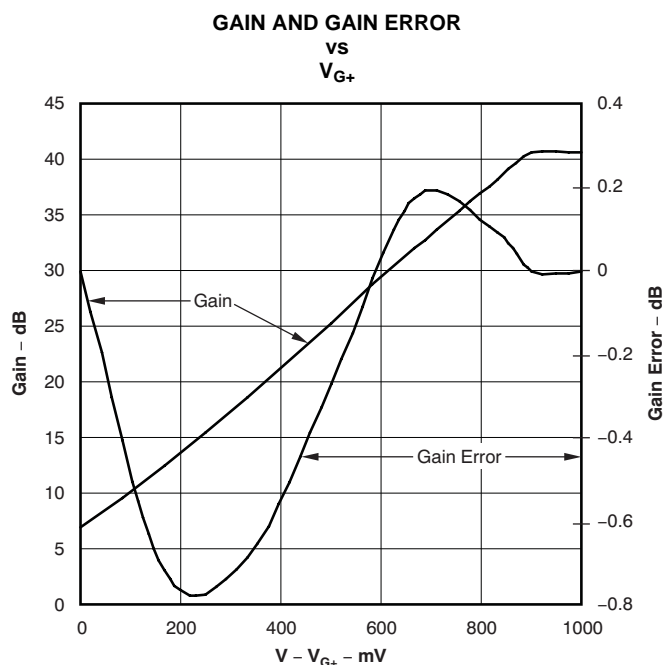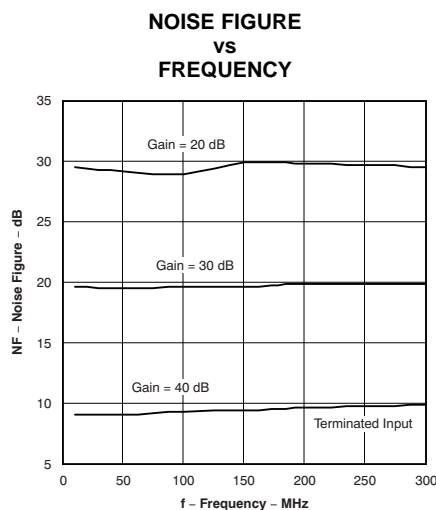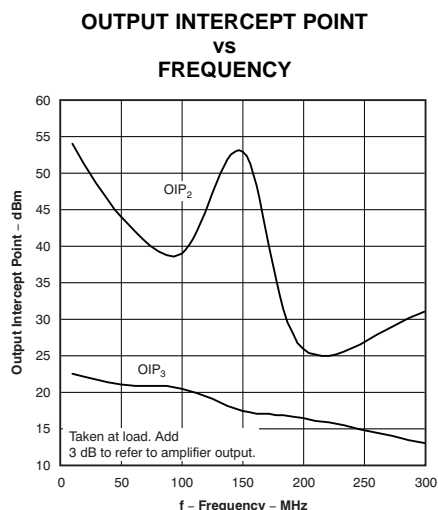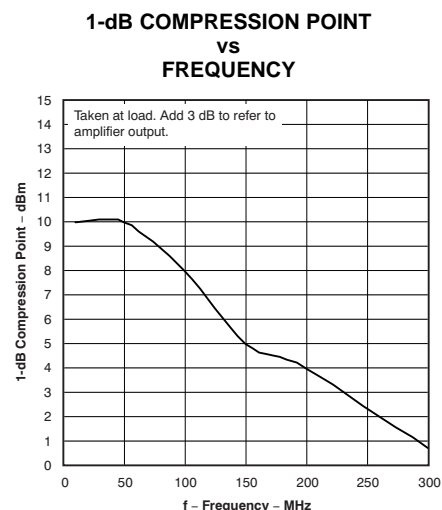
TYPICAL CHARACTERISTICS (continued)

**TOTAL INPUT VOLTAGE NOISE
vs
FREQUENCY**
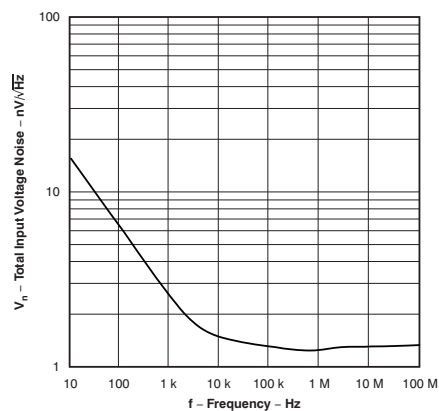
Figure 8.

**INTERMODULATION DISTORTION
vs
FREQUENCY**

Figure 9.

**HARMONIC DISTORTION
vs
FREQUENCY**

Figure 10.

**S-PARAMETERS
vs
FREQUENCY**

Figure 11.

**DIFFERENTIAL INPUT IMPEDANCE
OF MAIN AMPLIFIER
vs
FREQUENCY**

Figure 12.

**DIFFERENTIAL OUTPUT
IMPEDANCE OF MAIN AMPLIFIER
vs
FREQUENCY**

Figure 13.

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TEXAS INSTRUMENTS
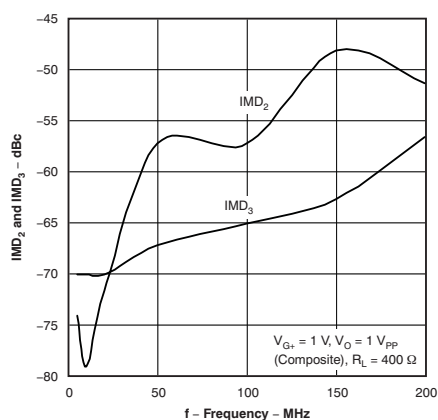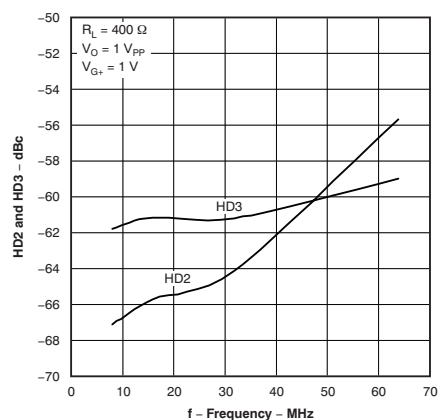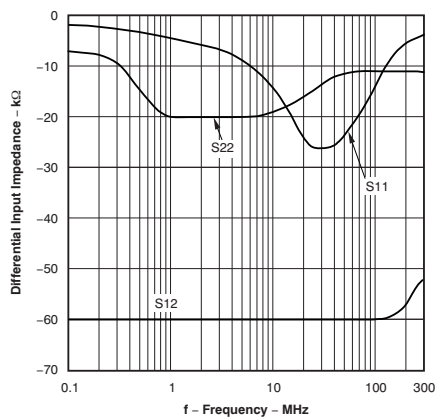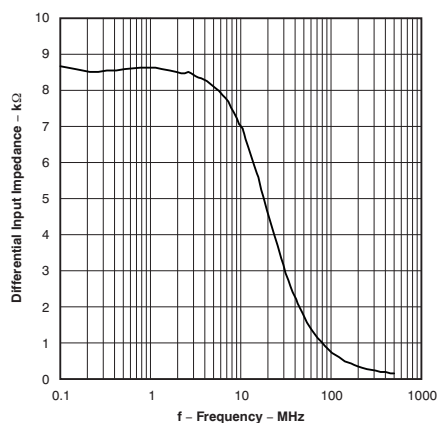
TYPICAL CHARACTERISTICS (continued)

**V_{G+} INPUT IMPEDANCE
vs
FREQUENCY**

Figure 14.

**V_{OCM} INPUT IMPEDANCE
vs
FREQUENCY**
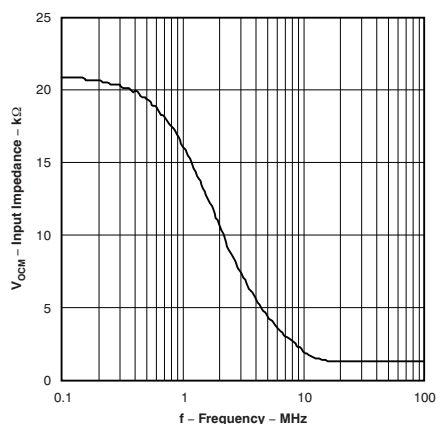
Figure 15.

**COMMON-MODE REJECTION RATIO
vs
FREQUENCY**

Figure 16.
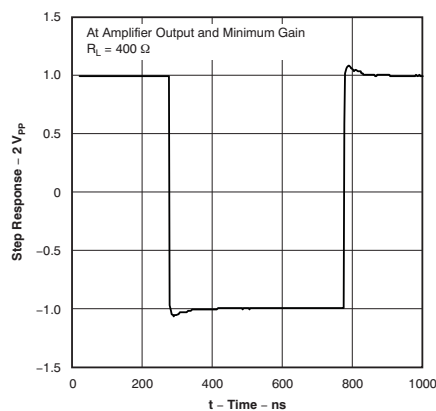
STEP RESPONSE

Figure 17.

STEP RESPONSE: RISING EDGE
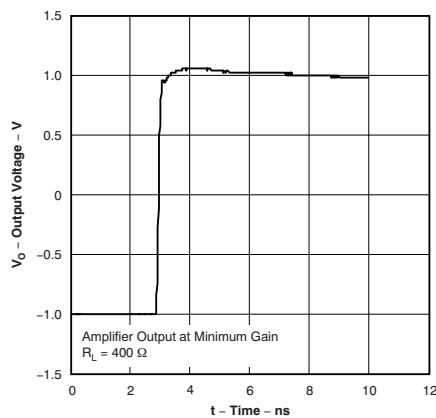
Figure 18.

STEP RESPONSE: FALLING EDGE

Figure 19.

Product Folder Link(s): THS7530
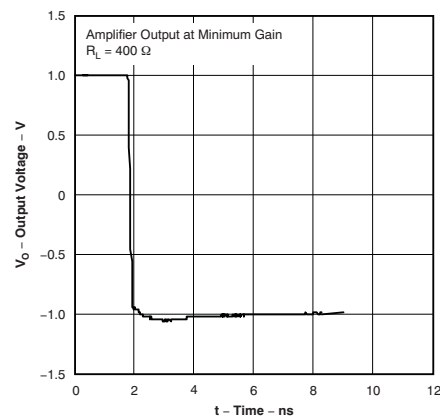
APPLICATION INFORMATION

The THS7530 is designed for nominal 5-V power supply from V_{S+} to V_{S-}.

The amplifier has fully differential inputs, V_{IN+} and V_{IN-}, and fully differential outputs, V_{OUT+} and V_{OUT-}. The inputs are high impedance and outputs are low impedance. External resistors are recommended for impedance matching and termination purposes.

The inputs and outputs can be dc-coupled, but for best performance, the input and output common-mode voltage should be maintained at the midpoint between the two supply pins. The output common-mode voltage is controlled by the voltage applied to V_{OCM}. Left unterminated, V_{OCM} is set to midsupply by internal resistors. A 0.1-μF bypass capacitor should be placed between V_{OCM} and ground to reduce common-mode noise. The input common-mode voltage defaults to midrail when left unconnected. For voltages other than midrail, V_{OCM} must be biased by external means. V_{IN+} and V_{IN-} both require a nominal 30-μA bias current for proper operation. Therefore, ensure equal input impedance at each input to avoid generating an offset voltage that varies with gain.

Voltage applied from V_{G-} to V_{G+} controls the gain of the part with 38.8-dB/V gain slope. The input can be differential or single ended. V_{G-} must be maintained within −0.6 V and +0.8 V of V_{S-} for proper operation. The negative gain input should typically be tied directly to the negative power supply.

V_{CL+} and V_{CL-} are inputs that limit the output voltage swing of the amplifier. The voltages applied set an absolute limit on the voltages at the output. Input voltages at V_{CL+} and V_{CL-} clamp the output, ensuring that neither output exceeds those values.

The power-down input is a TTL compatible input, referenced to the negative supply voltage. A logic low puts the THS7530 in power-saving mode. In power-down mode the part consumes less than 1-mA current, the output goes high impedance, and a high amount of isolation is maintained between the input and output.

Power-supply bypass capacitors are required for proper operation. A 6.8-μF tantalum bulk capacitor is recommended if the amplifier is located far from the power supply and may be shared among other devices. A ceramic 0.1-μF capacitor is recommended within 0.1-in of the device power pin. The ceramic capacitors should be located on the same layer as the amplifier to eliminate the use of vias between the capacitors and the power pin.

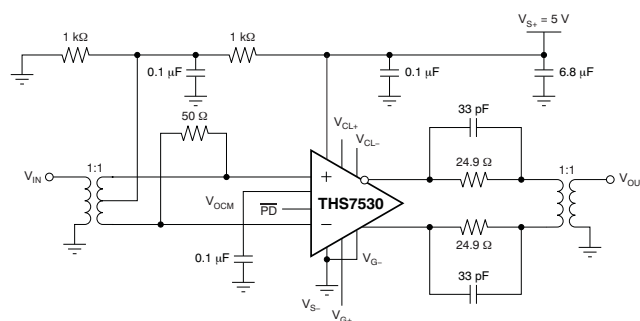Figure 20 through Figure 24 show some basic circuit configurations.

Figure 20. EVM Schematic: Designed for Use with Typical 50-Ω RF Test Equipment
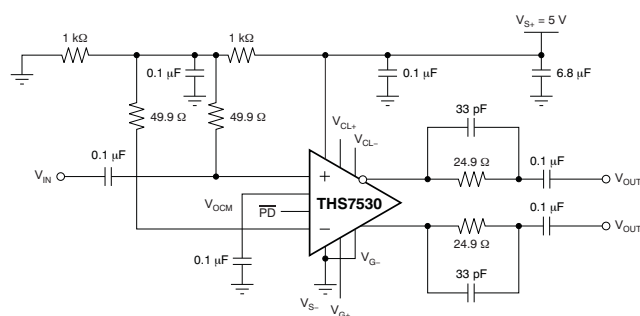

Figure 21. AC-Coupled Single-Ended Input with AC-Coupled Differential Output
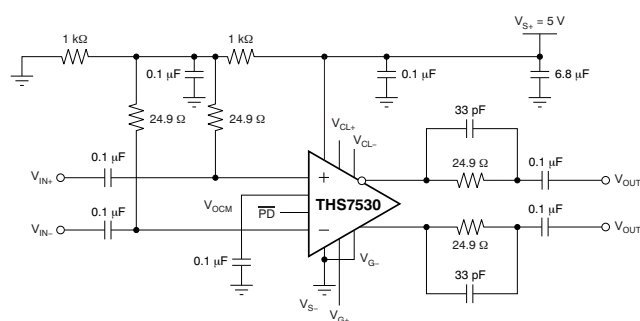

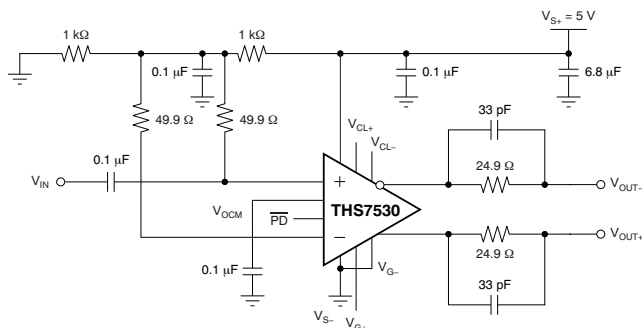**Figure 22. AC-Coupled Differential Input with AC-Coupled Differential Output**

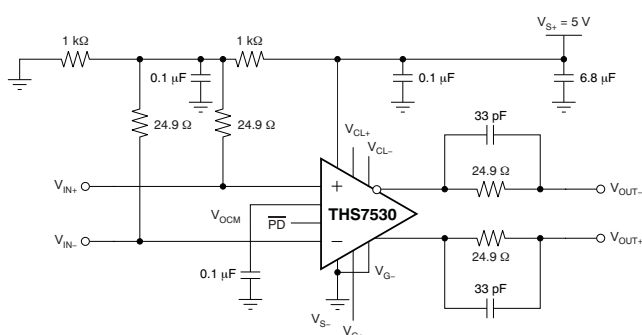**Figure 23. DC-Coupled Single-Ended Input with DC-Coupled Differential Output**

Figure 24. DC-Coupled Differential Input with DC-Coupled Differential Output

LAYOUT CONSIDERATIONS

The THS7530 comes in a thermally-enhanced PowerPAD™ package. Figure 25 shows the recommended number of vias and thermal land size recommended for best performance. Thermal vias connect the thermal land to internal or external copper planes and should have a drill diameter sufficiently small so that the via hole is effectively plugged when the barrel of the via is plated with copper. This plug is needed to prevent wicking the solder away from the interface between the package body and the thermal land on the surface of the board during solder reflow. The experiments conducted jointly with Solectron Texas indicate that a via drill diameter of 0,33 mm (13 mils, or .013 in) or smaller works well when 1-ounce copper is plated at the surface of the board and simultaneously plating the barrel of the via. If the thermal vias are not plugged when the copper plating is performed, then a solder mask material should be used to cap the vias with a dimension equal to the via diameter + 0,1 mm minimum. This prevents the solder from being wicked through the thermal via and potentially creating a solder void in the region between the package bottom and the thermal land on the surface of the PCB.
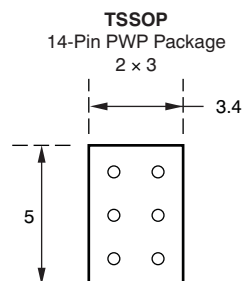

Figure 25. Recommended Thermal Land Size and Thermal Via Patterns (Dimensions in mm)

See TI's Technical Brief titled, *PowerPAD™ Thermally Enhanced Package* (SLMA002) for a detailed discussion of the PowerPAD™ package, its dimensions, and recommended use.

THEORY OF OPERATION

Figure 26 shows a simplified schematic of the THS7530.

The input architecture is a modified Gilbert cell. The output from the Gilbert cell is converted to a voltage and buffered to the output as a fully-differential signal. A summing node between the outputs is used to compare the output common-mode voltage to the V_{OCM} input. The V_{OCM} error amplifier then servos the output common-mode voltage to maintain it equal to the V_{OCM} input. Left unterminated, V_{OCM} is set to midsupply by internal resistors.

The gain control input is conditioned to give linear-in-dB gain control (block H). The gain control input is a differential signal from 0 V to 0.9 V which varies the gain from 11.6 dB to 46.5 dB.

V_{CL+} and $V_{CL−}$ provide inputs that limit the output voltage swing of the amplifier.
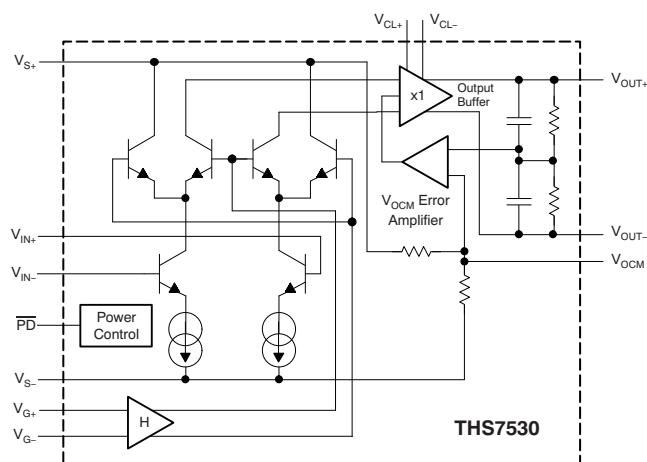

Figure 26. THS7530 Simplified Schematic

Product Folder Link(s): THS7530

SPICE MODEL

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* Texas Instruments Incorporated hereby grants the user of this SPICE Macro-model a
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*
* THS7530 SUBCIRCUIT
* HIGH SPEED FULLY DIFFERENTIAL VARIABLE AMPLIFIER
* WRITTEN 11/26/02
* VG- is tied to VS- and output clamping is not modeled
* CONNECTIONS: IN+
* |  IN-
* |  |  VS+
* |  |  |  VS-
* |  |  |  |  OUT-
* |  |  |  |  |  OUT+
* |  |  |  |  |  |  VOCM
* |  |  |  |  |  |  |  VG+
* |  |  |  |  |  |  |  |
.SUBCKT THS7530 1 2 3 4 5 6 7 8
*
*INPUT*
Q1 122 1 101 NPN_IN 16
Q2 123 2 102 NPN_IN 16
R1 102 101 25
I1 101 4 DC 4.85e-3
I2 102 4 DC 4.85e-3
*QUAD*
Q3 132 120 122 NPN 16
Q4 121 119 122 NPN 16
Q5 132 119 123 NPN 16
Q6 121 120 123 NPN 16
R2 132 3 250
R3 121 3 250
*CURRENT AMP*
F1 128 129 VF1 6
VF1 132 121 0V
*Z NODE*
R4 128 129 2k
I3 129 4 DC 0.75e-3
I4 128 4 DC 0.75e-3
V9 128 328 0.7
V10 129 329 0.7
```

```
*FREQUENCY SHAPING*
E3 131 0 329 0 1
R5 131 140 30
L3 140 133 7.5n
C6 133 0 24p
E4 130 0 328 0 1
R9 130 141 30
L4 141 125 10n
C7 125 0 27p
*OUTPUT BUFFER*
Q9 4 133 117 PNP 5.12
Q10 3 133 127 NPN 5.12
Q11 3 117 134 NPN 81.92
Q12 4 127 135 PNP 81.92
Q13 4 125 116 PNP 5.12
Q14 3 125 126 NPN 5.12
Q15 3 116 136 NPN 81.92
Q16 4 126 137 PNP 81.92
R6 138 134 5
R7 135 138 5
R10 139 136 5
R11 137 139 5
I5 3 117 DC 0.4e-3
I6 127 4 DC 0.4e-3
I7 3 116 DC 0.4e-3
I8 126 4 DC 0.4e-3
*OUTPUT Z*
R8 113 138 2
R12 115 139 2
L1 113 5 4n
L2 115 6 4n
C1 6 5 2p
*VOCM
Rcm1 115 114 8k
Ccm1 115 114 0.1p
Rcm2 114 113 8k
Ccm2 114 113 0.1p
E1 118 0 114 7 1e3
Rtop 3 7 50k
Rbot 4 7 50k
Q7 128 118 3 PNP 16
Q8 129 118 3 PNP 16
*GAIN CONTROL*
V8 235 8 0.454
E5 231 0 235 4 0.51
E6 232 0 POLY(1) 231 0 0.0 1 1 0.5 3.5
E7 233 0 232 0 0.115
E8 234 0 POLY(1) 233 0 0.0 0 1 0 0.333
E9 120 119 234 0 0.42
V7 3 120 1.6
Rsupply 3 4 310
.MODEL NPN_IN NPN
+ KF=1E-12
.MODEL NPN NPN
.MODEL PNP PNP
.ENDS
```

Product Folder Link(s): *THS7530*

REVISION HISTORY

PACKAGE OPTION ADDENDUM

PACKAGING INFORMATION

Orderable Device	Status [1]	Package Type	Package Drawing	Pins	Package Qty	Eco Plan [2]	Lead/Ball Finish	MSL Peak Temp [3]
THS7530PWP	ACTIVE	HTSSOP	PWP	14	90	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
THS7530PWPG4	ACTIVE	HTSSOP	PWP	14	90	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
THS7530PWPR	ACTIVE	HTSSOP	PWP	14	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR
THS7530PWPRG4	ACTIVE	HTSSOP	PWP	14	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR

[1] The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

[2] Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.
TBD: The Pb-Free/Green conversion plan has not been defined.
Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.
**Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.
Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

[3] MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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PACKAGE MATERIALS INFORMATION

TAPE AND REEL INFORMATION

REEL DIMENSIONS
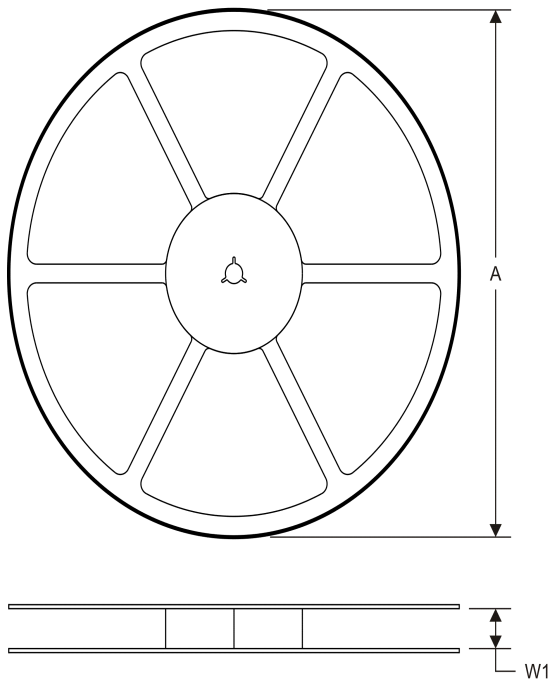
TAPE DIMENSIONS
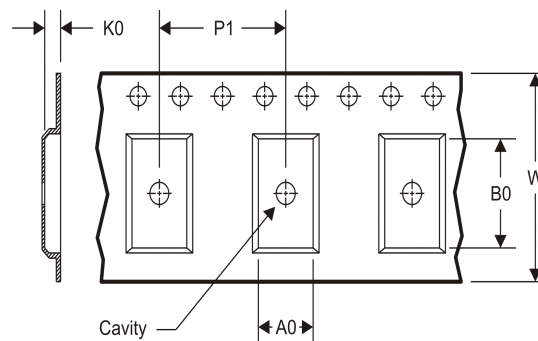
A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

TAPE AND REEL INFORMATION

*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
THS7530PWPR	HTSSOP	PWP	14	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1

TAPE AND REEL BOX DIMENSIONS

*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
THS7530PWPR	HTSSOP	PWP	14	2000	367.0	367.0	35.0

PWP (R–PDSO–G14)   PowerPAD™ PLASTIC SMALL OUTLINE
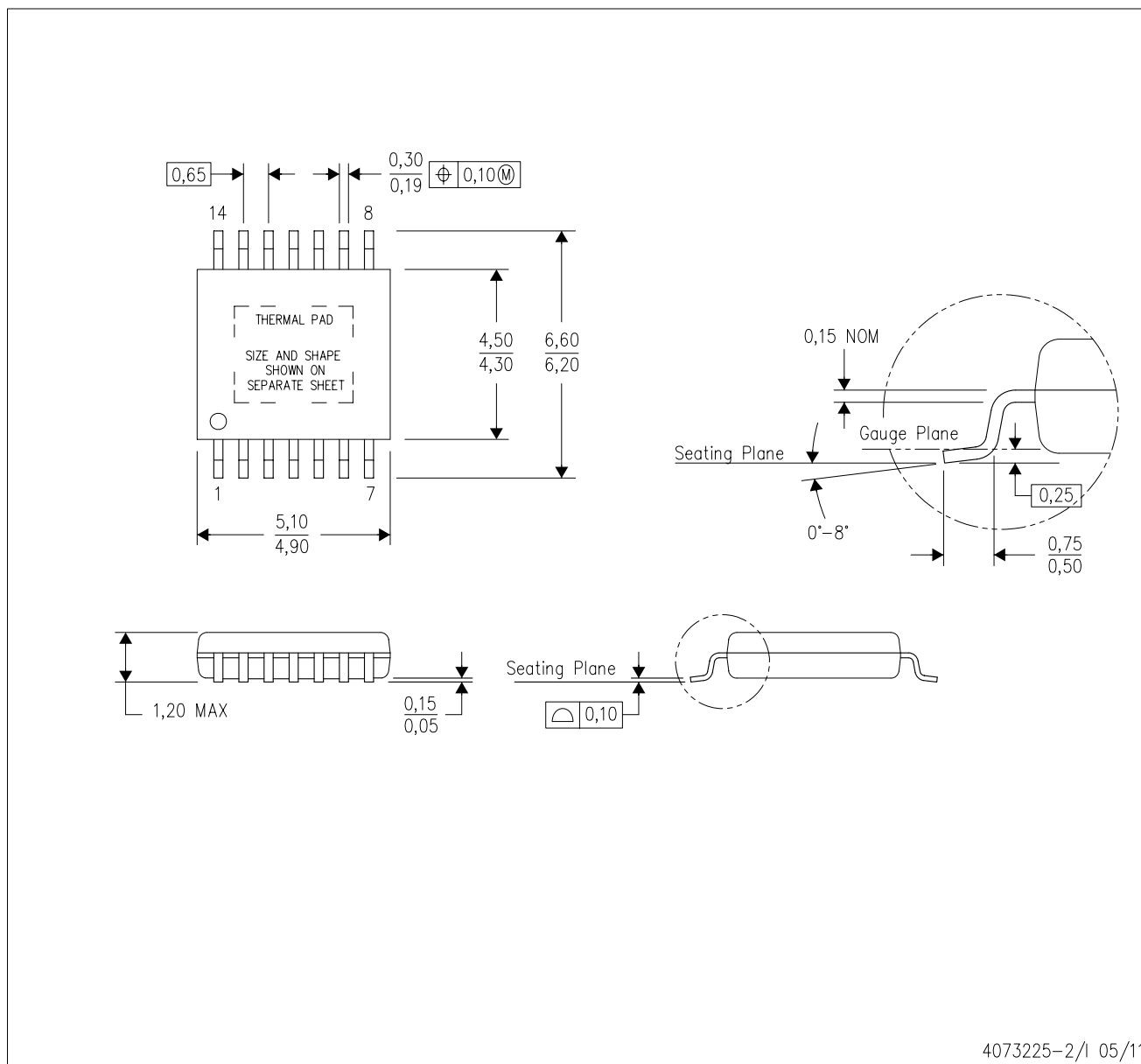
4073225–2/I 05/11

NOTES: A.   All linear dimensions are in millimeters.
         B.   This drawing is subject to change without notice.
         C.   Body dimensions do not include mold flash or protrusions. Mold flash and protrusion shall not exceed 0.15 per side.
         D.   This package is designed to be soldered to a thermal pad on the board. Refer to Technical Brief, PowerPad
              Thermally Enhanced Package, Texas Instruments Literature No. SLMA002 for information regarding
              recommended board layout. This document is available at www.ti.com <http://www.ti.com>.
         E.   See the additional figure in the Product Data Sheet for details regarding the exposed thermal pad features and dimensions.
         E.   Falls within JEDEC MO–153

PowerPAD is a trademark of Texas Instruments.

PWP (R-PDSO-G14)   PowerPAD™ SMALL PLASTIC OUTLINE

THERMAL INFORMATION

This PowerPAD™ package incorporates an exposed thermal pad that is designed to be attached to a printed circuit board (PCB). The thermal pad must be soldered directly to the PCB. After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For additional information on the PowerPAD package and how to take advantage of its heat dissipating abilities, refer to Technical Brief, PowerPAD Thermally Enhanced Package, Texas Instruments Literature No. SLMA002 and Application Brief, PowerPAD Made Easy, Texas Instruments Literature No. SLMA004. Both documents are available at www.ti.com.

The exposed thermal pad dimensions for this package are shown in the following illustration.

Exposed Thermal Pad

$\dfrac{2,46}{1,65}$

$\dfrac{2,31}{1,35}$

14   8

1   7

Top View

Exposed Thermal Pad Dimensions

4206332-2/AC 07/12

NOTE: A. All linear dimensions are in millimeters

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PWP (R−PDSO−G14) PowerPAD™ PLASTIC SMALL OUTLINE

Example Board Layout
Via pattern and copper pad size
may vary depending on layout constraints

Stencil Openings
Based on a stencil thickness
of .127mm (.005inch).
Reference table below for other
solder stencil thicknesses

Increasing copper area will
enhance thermal performance
(See Note D)

4x1,5 ⟶| |⟵ |⟵ 12x0,65

solder mask
over copper

2,46 3,4 5,6

3x1,5
6x∅0,33

Example Solder Mask
Defined Pad
(See Note C, D)

2,31
5,0

Example
Non Soldermask Defined Pad

14x0,25 ⟶| |⟵

14x1,55

5,6 2,46 Y

X

(See Note E)

2,31

12x0,65 ⟶| |⟵

Example
Solder Mask Opening
(See Note F)

0,3

1,6

0,07
All Around

Pad Geometry

Center Power Pad Solder Stencil Opening		
Stencil Thickness	X	Y
0.1mm	2.5	2.65
0.127mm	2.31	2.46
0.152mm	2.15	2.3
0.178mm	2.05	2.15

4207609−2/R 07/12

NOTES: A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Customers should place a note on the circuit board fabrication drawing not to alter the center solder mask defined pad.
D. This package is designed to be soldered to a thermal pad on the board. Refer to Technical Brief, PowerPad
    Thermally Enhanced Package, Texas Instruments Literature No. SLMA002, SLMA004, and also the Product Data Sheets
    for specific thermal information, via requirements, and recommended board layout. These documents are available at
    www.ti.com <http://www.ti.com>. Publication IPC−7351 is recommended for alternate designs.
E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should
    contact their board assembly site for stencil design recommendations. Example stencil design based on a 50% volumetric
    metal load solder paste. Refer to IPC−7525 for other stencil recommendations.
F. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

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